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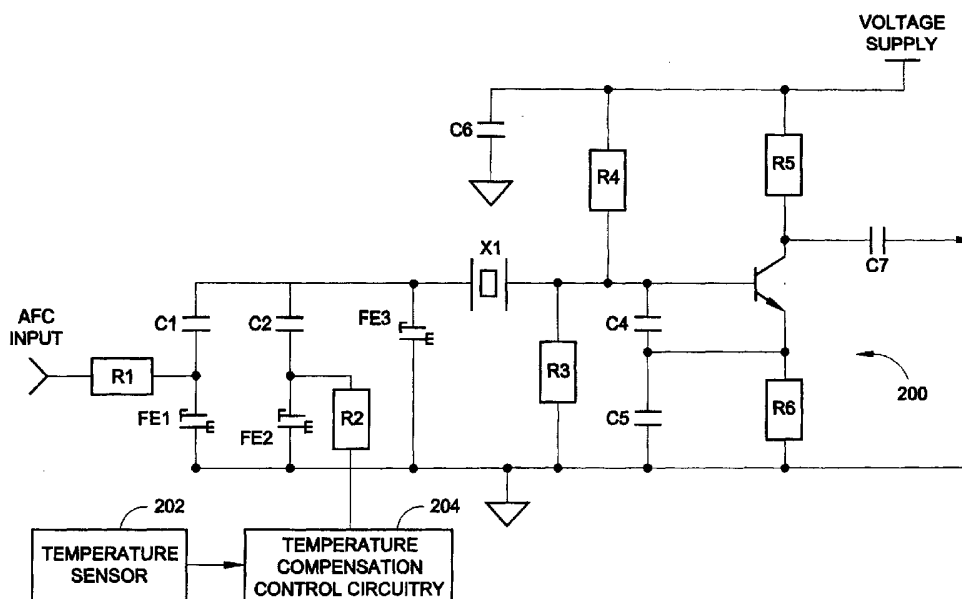
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(54) Title: TUNABLE VOLTAGE-CONTROLLED TEMPERATURE-COMPENSATED CRYSTAL OSCILLATOR



(57) Abstract: A crystal oscillator having tunable ferroelectric components. A first ferroelectric capacitor is coupled to an automatic frequency control line for fine tuning the reference frequency. A second ferroelectric capacitor is coupled to temperature compensation control circuitry that applies a correction voltage to the second capacitor to vary the reference frequency in response to ambient temperature changes. A third ferroelectric capacitor has a capacitance that is adjusted and fixed during manufacture to set the initial tolerance of the crystal oscillator at ambient temperature.

## **TUNABLE VOLTAGE-CONTROLLED TEMPERATURE- COMPENSATED CRYSTAL OSCILLATOR**

### **Cross-Reference to Related Applications**

This application claims the benefit of U.S. Provisional Application 60/283,093, filed April 11, 2001, which is hereby incorporated by reference. In addition, this application relates to the following U.S. applications, which are hereby incorporated by reference: 09/904,631 filed on July 13, 2001, by Stanley S. Tonicich entitled "Ferro-Electric Tunable Filter"; 09/912,753 filed on July 24, 2001 by Stanley S. Tonicich entitled "Tunable Ferro-Electric Multiplexer"; 09/927,732 filed on August 8, 2001, by Stanley S. Tonicich entitled "Low Loss Tunable Ferro-Electric Device and Method of Characterization"; 09/927,136 filed on August 10, 2001, by Stanley S. Tonicich entitled "Tunable Matching Circuit"; 10/044,522 filed on January 11, 2002, by Stanley S. Tonicich entitled "Tunable Planar Capacitor"; 10/077,654 filed on February 14, 2002, by Stanley S. Tonicich entitled "Tunable Isolator Matching Circuit"; 10/076,171 filed on February 12, 2002, by Stanley S. Tonicich entitled "Antenna Interface Unit"; 10/075,896 filed February 12, 2002, by Stanley S. Tonicich entitled "Tunable Antenna Matching Circuit"; 10/075,727 filed February 12, 2002, by Stanley S. Tonicich and Tim Forrester entitled "Tunable Low Noise Amplifier"; 10/075,507 filed on February 12, 2002, by Stanley S. Tonicich entitled "Tunable Power Amplifier Matching Circuit".

### **Field of the Invention**

The present invention relates generally to tunable electronic devices and components and, more particularly, to crystal oscillators incorporating tunable ferroelectric components.

### **Background of the Invention**

Radio frequency bandwidth is a scarce resource that is highly valued and is becoming increasingly congested. Ever-increasing numbers of users are attempting to co-exist and to pass ever-increasing amounts of information through the finite amount of bandwidth that is available. The radio spectrum is divided into frequency bands that are allocated for specific uses. In the United States, for example, all FM radio stations transmit in the 88-108 MHz band and all AM radio stations transmit in the 535 kHz-1.7 MHz band. The frequency band around 900 MHz is

reserved for wireless phone transmissions. A frequency band centered around 2.45 GHz has been set aside for the new Bluetooth technology. Hundreds of other wireless technologies have their own band of the radio spectrum set aside, from baby monitors to deep space communications.

5            Communications within a given frequency band occur on even more narrowly and precisely defined channels within that band. Hence, in virtually any wireless communication system or device, frequency agility is required and accurate frequency generation is of critical importance. Voltage controlled oscillators (VCOs) can generate a large range of frequencies, but are problematic in that they are unstable and tend to drift. Crystal oscillators, conversely,  
10           provide excellent frequency stability but can be used only over the narrow frequency range of the particular quartz crystal contained in the oscillator. A phase-locked loop (PLL) is a commonly used frequency synthesis technique that takes advantage of both the flexibility of a voltage controlled oscillator and the stability of a crystal oscillator.

**Figure 1** depicts a typical frequency synthesis circuit including a PLL 100 and reference  
15           crystal oscillator 200. PLL 100 operates in a well-known fashion. Briefly, VCO 108 generates a range of output frequencies via variation of a DC control voltage input to the VCO. The output of VCO 108 is fed back to phase comparator 102, which also receives an input from crystal oscillator 200. The VCO and crystal oscillator inputs to comparator 102 are combined, and any difference in phase/frequency results in a DC voltage output. The output of comparator 102 is  
20           coupled back to the input of VCO 108 via charge pump 104 and loop filter 106. The greater the frequency/phase difference that exists between the two signals, the larger the output voltage from comparator 102, and the larger the adjustment that is made to the VCO output frequency. Hence, the output of VCO 108 is driven to, and eventually locks onto, the frequency of crystal oscillator 200. Divider 110 is positioned in the feedback path between VCO 108 and phase comparator  
25           102. It is typically a programmable frequency divider that divides the VCO frequency down to the reference frequency produced by crystal oscillator 200. Hence, a large range of output frequencies can be generated and frequency lock still maintained by manipulation of the divide-by number.

             Crystal oscillator 200 uses a quartz crystal to provide a fixed and stable reference  
30           frequency. Since temperature affects the rate at which a crystal vibrates, crystal oscillators often include a temperature compensation network that senses the ambient temperature and “pulls” the crystal frequency to prevent frequency drift over a temperature range. A temperature

compensated crystal oscillator is referred to as a TCXO. Crystal oscillators, like voltage controlled oscillators, can also be made tunable over the frequency range (albeit much smaller) of the crystal by application of a control voltage. A voltage controlled crystal oscillator is referred to as a VCXO. A crystal oscillator that combines the attributes of voltage control and temperature compensation is referred to as a VC-TCXO.

In recent years, VC-TCXO designs have been required to comply with significantly more demanding specifications. VC-TCXOs are typically required to remain frequency stable to within  $\pm 2.5$  parts per million (ppm) over a temperature range of  $-30^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$ . Moreover, their initial accuracy or tolerance at ambient temperature must be within  $\pm 1.5$  ppm.

Modern communication devices also impose very high spectral purity and phase noise demands on the VC-TCXO. Phase noise affects the receiver's ability to reject unwanted signals on nearby channels. It is the ratio of the output power divided by the noise power at a specified offset and is expressed in dBc/Hz. The reference frequency produced by a VC-TCXO may be used to phase lock an output frequency that is one-hundred times or more greater. Since phase noise performance is degraded by a factor of  $20 \log N$ , where  $N$  is the frequency multiplier or divide-by number, close in phase noise performance (i.e. at offsets of less than 100 Hz) exceeding -90dBc is required.

Close in phase noise performance is especially important in FM systems and in position location systems. In FM systems, close in phase noise directly degrades the audio quality and manifests itself as an audio hiss. In position location systems, such as those used to receive GPS signals, close in phase noise may manifest itself as positional inaccuracy or receiver sensitivity impairment. Receiver sensitivity impairment is due to the short term frequency or phase jitter of the reference oscillator caused by the phase noise, and the subsequent inability of the receiver to accurately correlate for extended periods of time.

To meet these stringent accuracy and close in phase noise requirements, the VC-TCXO topology and components must be chosen with caution. The use of a dedicated integrated circuit (IC), a frequency control element and factory calibration are required. Each of these requirements adds considerable time and cost to production. Currently, only a handful of manufacturers world wide can economically produce VC-TCXOs meeting these requirements that are suitable for use in high volume consumer communication devices.

The  $Q$  of the oscillator quartz crystal alone can be as high as 50,000, meaning that additional losses of any significance at all in the resonator network will dramatically reduce the

overall Q and seriously degrade close in phase noise performance. One element that is particularly difficult to implement and control without degrading close in phase noise performance is the voltage controlled, frequency-tuning element associated with the crystal. In a VC-TCXO, this element usually takes the form of a voltage dependent capacitor, commonly referred to as a variable capacitance diode, varicap diode or varactor.

The operation of a varactor is well understood. When a reverse voltage is applied to a varactor, the insulation layer between the p-doped and n-doped semiconductor regions thickens. A depletion region that is essentially devoid of carriers forms and behaves as the dielectric of the capacitor. The depletion region increases as the reverse voltage across it increases, and since capacitance varies inversely as dielectric thickness, the junction capacitance decreases as the reverse voltage increases. Capacitance variations effected by control voltage variations effect corresponding variations in the resonant frequency of the oscillator.

Unfortunately, a typical varactor has a relatively low Q due to its intrinsic series resistance, which may be as much as several ohms. The Q of a varactor can be expressed as  $X_c / R_s$ , where  $X_c$  is the reactance of the varactor ( $1/[2 \cdot \pi \cdot f \cdot c]$ ) and  $R_s$  is the effective series resistance of the varactor. A capacitance of 5 pF at a frequency of 1.5 GHz results in a reactance  $X_c$  of  $21.22\Omega$ . If the effective series resistance  $R_s$  of the varactor is  $0.5\Omega$ , the resultant Q is 42.44. When compared to the extremely high Q of the crystal itself, it can be seen how much this will degrade the overall Q of the oscillator. Clearly, the effective series resistance of the varactor poses a problem and a tuning element having less series resistance will have a highly direct and positive impact on the overall Q.

Another problem with use of varactors is their non-linear transfer function (applied voltage versus capacitance). **Figure 2** is a chart plotting the capacitance of a typical varactor versus a common tuning range for this component in a mobile phone (0.3V to 2.7V). As can be seen, it is not a linear relation. Below 0.5V, unit voltage changes lead to much greater unit capacitance changes. Consequently, the MHz/volt frequency shift of the oscillator is not constant across the tuning range.

Another problem associated with the varactor is that, since it is a reverse-biased diode junction, it is important that the applied AC signal does not overcome the bias voltage and result in heavy forward conduction of the diode. If this occurs the Q of the resonator will be dramatically lowered and various oscillator parameters such as phase noise and general spectral

purity will be seriously impacted. In extreme cases, the oscillator may fail to maintain a continuous oscillation and degenerate into parasitic uncontrolled burst oscillations.

In view of the above, there is a need for a voltage controlled temperature compensated crystal oscillator employing frequency tuning elements without the attendant drawbacks of degraded phase noise performance and non-linear transfer function.

### **Summary of the Invention**

The present invention provides a voltage controlled temperature compensated crystal oscillator that incorporates a tunable ferroelectric capacitor to provide better phase noise performance and a more linear voltage/capacitance transfer function.

Accordingly, one embodiment of the invention provides a voltage controlled crystal oscillator. It comprises a crystal for generating a reference frequency, a ferroelectric capacitor having a variable capacitance, and a control line coupled to the ferroelectric capacitor for applying a control voltage to the capacitor. The control voltage varies the capacitance which varies the reference frequency generated by the crystal.

Another embodiment of the invention provides a temperature compensated crystal oscillator. It comprises a crystal for generating a reference frequency, a ferroelectric capacitor having a variable capacitance, a temperature sensor and temperature compensation control circuitry coupled to the temperature sensor and to the ferroelectric capacitor. The control circuitry applies an appropriate correction voltage to the ferroelectric capacitor in response to changes in temperature sensed by the temperature sensor. The correction voltage varies the capacitance of the ferroelectric capacitor which, in turn, varies the reference frequency generated by the crystal.

Another embodiment of the invention provides a crystal oscillator. It comprises a crystal for generating a reference frequency and a ferroelectric capacitor having a capacitance that is adjusted and then fixed during manufacture to set the initial tolerance of the crystal oscillator at ambient temperature.

Another embodiment of the invention provides a voltage controlled temperature compensated crystal oscillator. A fine tuning ferroelectric has a variable capacitance and is coupled to an automatic frequency control line that applies a control voltage to vary the capacitance of the fine tuning capacitor which, in turn, fine tunes the reference frequency generated by the crystal. A temperature compensating ferroelectric capacitor has a variable

capacitance and is coupled to a temperature sensor and temperature compensation control circuitry. The control circuitry applies an appropriate correction voltage to the temperature compensating capacitor in response to changes in temperature sensed by the temperature sensor to vary the capacitance of the temperature compensating capacitor which, in turn, varies the reference frequency generated by the crystal in response to ambient temperature changes. A third ferroelectric capacitor has a capacitance that is adjusted and then fixed during manufacture to set the initial tolerance of the crystal oscillator at ambient temperature.

Other features, objects and implementations of the invention will be or will become apparent to one with skill in the art upon examination of the following figures and detailed description. All such additional features, objects and implementations are intended to be included within this description, to be within the scope of the invention and to be protected by the accompanying claims.

### **Brief Description of the Drawings**

**Figure 1** is a schematic of a conventional frequency synthesis circuit including a phase-locked loop and a temperature compensated voltage controlled crystal oscillator.

**Figure 2** is a graph plotting capacitance versus applied control voltage for a typical varactor.

**Figure 3** is a graph plotting capacitance versus applied control voltage for a ferroelectric capacitor according to the present invention.

**Figure 4** is a schematic of a ferroelectric tuned voltage controlled temperature compensated crystal oscillator according to the present invention.

### **Detailed Description of the Invention**

Crystal oscillators currently in use typically employ varicap diodes or varactors as the frequency tuning device. These oscillators exhibit compromised phase noise performance and non-linear capacitance/control voltage transfer functions. In order to overcome these shortcomings, the present invention provides an oscillator employing a ferroelectric capacitor, rather than a varicap diode, as the tuning device. Ferroelectric capacitors may be provided in the

crystal oscillator for any or all of voltage control, temperature compensation and/or setting the initial tolerance of the capacitor.

The background, advantages, topologies and test methods associated with ferroelectric capacitors are fully set forth in commonly owned United States provisional application serial no. 60/283,093 filed on April 11, 2001, as well as commonly owned related United States application nos. 09/904,631 filed on July 13, 2001, by Stanley S. Toncich entitled "Ferro-Electric Tunable Filter"; 09/912,753 filed on July 24, 2001 by Stanley S. Toncich entitled "Tunable Ferro-Electric Multiplexer"; 09/927,732 filed on August 8, 2001, by Stanley S. Toncich entitled "Low Loss Tunable Ferro-Electric Device and Method of Characterization"; 09/927,136 filed on August 10, 2001, by Stanley S. Toncich entitled "Tunable Matching Circuit"; 10/044,522 filed on January 11, 2002, by Stanley S. Toncich entitled "Tunable Planar Capacitor"; 10/077,654 filed on February 14, 2002, by Stanley S. Toncich entitled "Tunable Isolator Matching Circuit"; 10/076,171 filed on February 12, 2002, by Stanley S. Toncich entitled "Antenna Interface Unit"; 10/075,896 filed February 12, 2002, by Stanley S. Toncich entitled "Tunable Antenna Matching Circuit"; 10/075,727 filed February 12, 2002, by Stanley S. Toncich and Tim Forrester entitled "Tunable Low Noise Amplifier"; 10/075,507 filed on February 12, 2002, by Stanley S. Toncich entitled "Tunable Power Amplifier Matching Circuit", which are hereby incorporated by reference. Briefly, these applications disclose test methods utilizing narrowband resonant circuits that accurately measure and characterize the loss due to use of a ferroelectric material, and establish that ferroelectric components are not as lossy as previously thought. Previous testing methods and devices did not account for all loss mechanisms and it was therefore not possible to accurately determine the loss due to use of ferroelectric material. In one implementation, the narrowband resonant circuit used for testing is a microstrip resonator having a gap to define the capacitor, and a ferroelectric film deposited in the gap.

By employing proper testing methods and loss accounting mechanisms, tunable ferroelectric components can be optimized and designed for use in a wide variety of low loss applications and frequency agile circuits. The choice of topology is critical for attaining the best possible Q (lowest losses). Depending on the particular topology and materials that are employed, and the applicable frequency range, Qs of greater than 80, greater than 180 and even higher are attainable. Design procedures and implementation details are set forth for gap capacitors, overlay capacitors and interdigital capacitors. The lowest losses are achieved by



direct fabrication of the ferroelectric capacitor to the resonator or other RF circuitry. This eliminates added losses caused by attachment of the ferroelectric capacitor to a circuit.

**Figure 4** depicts a ferroelectric tuned voltage controlled temperature compensated crystal oscillator (VC-TCXO) 200 according to the present invention. VC-TCXO 200 has a layout similar to that of a conventional VC-TCXO design, but differs in that it employs ferroelectric components rather than varactors as the voltage controlled tuning devices. At least one ferroelectric component, and as many as three or more ferroelectric components, are utilized. VC-TCXO 200 illustrated in **Figure 4** includes three ferroelectric capacitors FE1, FE2 and FE3..

A variable ferroelectric capacitor has several advantages over a varicap diode. First, it has a much lower series resistance, typically by a factor of ten. This will directly result in a higher  $Q$  ( $Q = X_c / R_s$ , see discussion above) and better phase noise performance. Secondly, as plotted in **Figure 3**, the capacitance/applied voltage transfer function of a ferroelectric capacitor is essentially linear, thereby permitting the design of more optimum PLL loop filters. Finally, ferroelectric capacitors do not suffer from the forward bias conduction problems of varicap diodes.

The first potential use of a ferroelectric capacitor in a VC-TCXO is for automatic frequency control (AFC), that is, accurate control of the frequency produced by the VC-TCXO. This is also sometimes referred to as fine control or trimming of the oscillator frequency. Ferroelectric capacitor FE1 in VC-TCXO 200 is provided for fine or automatic frequency control. As can be seen in **Figure 4**, an AFC input voltage is applied to ferroelectric capacitor FE1 (via resistance R1). By varying the AFC input voltage, and hence the voltage applied to FE1, the capacitance of FE1 and thus the operating frequency of oscillator 200 is changed. The AFC input voltage may also be used in conjunction with capacitor FE1 to manually trim out any remaining initial tolerance error at ambient temperature.

The second potential use of a ferroelectric capacitor in a VC-TCXO is in conjunction with the temperature compensation function. VC-TCXO 200 comprises temperature compensation control circuitry 204. Based on ambient temperature measurements provided by temperature sensor 202 (a thermistor, or the like), control circuitry 204 applies an appropriate correction voltage to ferroelectric capacitor FE2, which in turn affects the capacitance of FE2 and hence the operating frequency of oscillator 200. Temperature compensation control circuitry may function in an analog or digital manner, but the end result is an analog voltage applied to FE2. In the digital case, which is the most common, a particular digital word is generated by

control circuitry 204 for a certain range of temperatures measured by sensor 202 (typically a five degree window). The digital word is provided to a digital to analog converter (either contained in circuitry 204 or interposed between circuitry 204 and FE2), which then applies a corresponding analog control voltage to FE2.

5       The third potential use of a ferroelectric capacitor in a VC-TCXO is for adjustment of the initial tolerance of the oscillator at ambient temperature. Typically, the initial tolerance is adjusted to within  $\pm 2$  ppm of the nominal frequency. In VC-TCXO 200, ferroelectric capacitor FE3 provides this function. In one implementation, FE3 is under the control of a simple digital to analog converter (not shown) whose value is set at the time of manufacture. This value is set  
10   in memory before any temperature compensation data is written by circuitry 204.

The use of ferroelectric components in VC-TCXO 200, in addition to providing a higher Q and better phase noise performance as described above, is also advantageous in that it results in a much higher device yield. Presently, during VC-TCXO manufacture, a number of fixed value capacitors are installed (a fixed value capacitor is conventionally used in place of  
15   ferroelectric capacitor FE3, for example) and tested in turn to set the initial frequency. Due to re-work issues, a capacitor value can be changed only two or three times before the whole VC-TCXO is rejected. The rejected VC-TCXOs add directly to the cost of those VC-TCXOs which pass all tests. By using ferroelectric tuning components rather than fixed value capacitors, this problem is essentially removed and a much higher yield results. Also, since ferroelectric  
20   components are electrically tuned rather than adjusted by manual or automated component replacement, the process of trimming the VC-TCXO is much quicker and further contributes to a lower unit cost.

Another advantage provided by the use of ferroelectric components is the ability to integrate more components onto the silicon chip. In a typical VC-TCXO, the crystal X1 and the  
25   fixed value capacitor employed (in place of ferroelectric capacitor FE3) cannot be integrated onto the chip. As described above, the fixed value capacitor is subject to an installation, testing and removal process and hence cannot be integrated with the rest of the circuit. Typically, the varactor diodes used (rather than ferroelectric capacitors FE1 and FE2) are not integrated onto the chip either.

30       In VC-TCXO 200, conversely, it is entirely feasible to integrate all components onto the silicon chip (with the exception of crystal X1). The ferroelectric material employed in capacitors FE1, FE2 and FE3 can be deposited during the normal integrated circuit fabrication process since

the FE deposition process is only a few microns thick and is compatible with existing microchip manufacturing processes. Although the ferroelectric tuning devices could be installed as stand alone components, it is preferred that they be integrated onto the chip. As described in the related applications referenced herein, integration of the ferroelectric components directly into the circuit reduces the loss that arises due to the connection process.

Other embodiments and implementations of the invention will be or will become apparent to one with skill in the art. All such additional embodiments and implementations are intended to be included within this description, to be within the scope of the invention and to be protected by the accompanying claims.

### Claims

1. A voltage controlled crystal oscillator comprising:

a crystal for generating a reference frequency;

a ferroelectric capacitor having a variable capacitance; and

5 a control line coupled to the ferroelectric capacitor for applying a control voltage to the capacitor, the control voltage varying the capacitance which, in turn, varies the reference frequency generated by the crystal.

2. A voltage controlled crystal oscillator as claimed in claim 1, wherein the control

10 voltage has a linear relation to the capacitance across the tuning range of the capacitor.

3. A voltage controlled crystal oscillator as claimed in claim 2, wherein the crystal oscillator exhibits close in phase noise performance exceeding -90 dBc.

15 4. A voltage controlled crystal oscillator as claimed in claim 1, and further comprising:

a second ferroelectric capacitor;

a temperature sensor; and

20 temperature compensation control circuitry coupled to the temperature sensor and to the second ferroelectric capacitor, the control circuitry applying an appropriate correction voltage to the second ferroelectric capacitor in response to changes in temperature sensed by the temperature sensor, the correction voltage varying the capacitance of the second ferroelectric capacitor which, in turn, varies the reference frequency generated by the crystal.

25 5. A voltage controlled crystal oscillator as claimed in claim 4, wherein the ferroelectric capacitors are integrated onto a silicon chip.

6. A temperature compensated crystal oscillator comprising

a crystal for generating a reference frequency;

30 a ferroelectric capacitor having a variable capacitance;

a temperature sensor; and

temperature compensation control circuitry coupled to the temperature sensor and to the ferroelectric capacitor, the control circuitry applying an appropriate correction voltage to the ferroelectric capacitor in response to changes in temperature sensed by the temperature sensor, the correction voltage varying the capacitance of the ferroelectric capacitor which, in turn, varies the reference frequency generated by the crystal.

7. A temperature compensated crystal oscillator as claimed in claim 6, wherein the temperature compensation control circuitry generates digital words corresponding to ranges of temperature sensed by the temperature sensor, and wherein the control circuitry further comprises a digital to analog converter for converting the digital word to the correction voltage to be applied to the ferroelectric capacitor.

8. A temperature compensated crystal oscillator as claimed in claim 6, and further comprising a second ferroelectric capacitor configured to adjust the initial tolerance of the oscillator at ambient temperature.

9. A temperature compensated crystal oscillator as claimed in claim 8, wherein the ferroelectric capacitors are integrated onto a silicon chip.

10. A crystal oscillator comprising:  
a crystal for generating a reference frequency; and  
a ferroelectric capacitor having a capacitance that is adjusted and then fixed during manufacture to set the initial tolerance of the crystal oscillator at ambient temperature.

11. A crystal oscillator as claimed in claim 10, wherein the initial tolerance is adjusted to within  $\pm 2$  ppm of the reference frequency.

12. A crystal oscillator as claimed in claim 10, and further comprising a digital to analog converter programmed to a value that is set at the time of manufacture and being coupled to the ferroelectric capacitor so that the capacitance of the ferroelectric capacitor is a constant reflective of the initial tolerance.

13. A crystal oscillator as claimed in claim 10, and further comprising: a  
second ferroelectric capacitor having a variable capacitance; and

a control line coupled to the second ferroelectric capacitor for applying a control voltage to the capacitor, the control voltage varying the capacitance which, in turn, fine tunes the  
5 reference frequency generated by the crystal.

14. A crystal oscillator as claimed in claim 13, wherein the ferroelectric capacitors are integrated onto a silicon chip.

10 15. A voltage controlled temperature compensated crystal oscillator comprising:  
a crystal for generating a reference frequency;  
a fine tuning ferroelectric capacitor having a variable capacitance;  
an automatic frequency control line coupled to the fine tuning ferroelectric capacitor for  
applying a control voltage to the fine tuning capacitor, the control voltage varying the  
15 capacitance of the fine tuning capacitor which, in turn, fine tunes the reference frequency  
generated by the crystal;

a temperature compensating ferroelectric capacitor having a variable capacitance;

a temperature sensor;

temperature compensation control circuitry coupled to the temperature sensor and to the  
20 temperature compensating capacitor, the control circuitry applying an appropriate correction  
voltage to the temperature compensating capacitor in response to changes in temperature sensed  
by the temperature sensor, the correction voltage varying the capacitance of the temperature  
compensating capacitor which, in turn, varies the reference frequency generated by the crystal in  
response to ambient temperature changes; and

25 a third ferroelectric capacitor having a capacitance that is adjusted and then fixed during  
manufacture to set the initial tolerance of the crystal oscillator at ambient temperature.

16. A voltage controlled temperature compensated crystal oscillator as claimed in  
claim 15 that exhibits close in phase noise performance exceeding -90 dBc.

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17. A voltage controlled temperature compensated crystal oscillator as claimed in  
claim 15, wherein the temperature compensation control circuitry generates digital words

corresponding to ranges of temperature sensed by the temperature sensor, and wherein the control circuitry further comprises a digital to analog converter for converting the digital word to the correction voltage to be applied to the temperature compensating ferroelectric capacitor.

5           18.    A voltage controlled temperature compensated crystal oscillator as claimed in claim 15, wherein the initial tolerance is adjusted to within  $\pm 2$  ppm of the reference frequency, and further comprising a digital to analog converter programmed to a value that is set at the time of manufacture and that is coupled to the third ferroelectric capacitor so that the capacitance of the third ferroelectric capacitor is a constant reflective of the initial tolerance.

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          19.    A voltage controlled temperature compensated crystal oscillator as claimed in claim 15, wherein all ferroelectric capacitors are directly integrated onto a silicon chip.

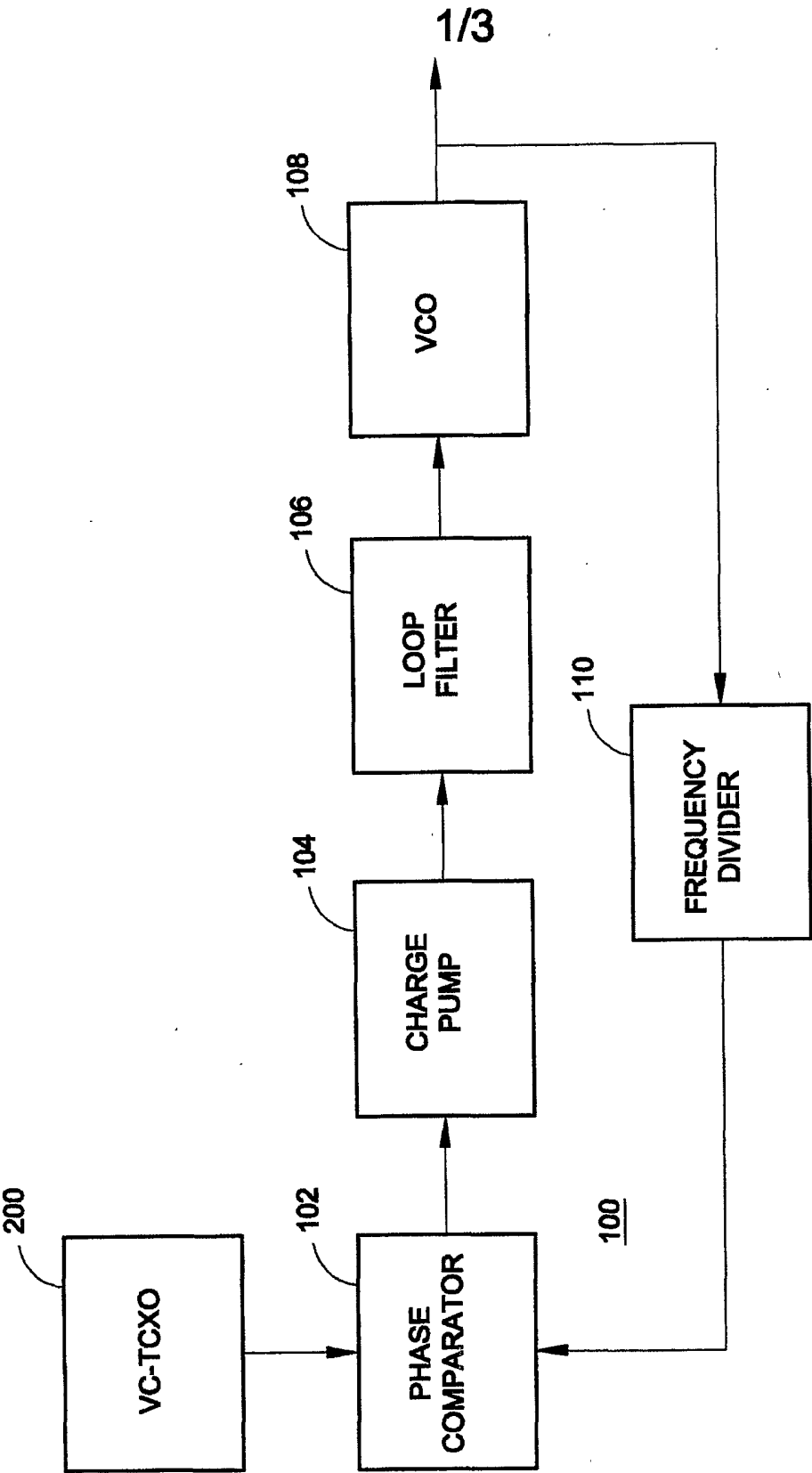


FIG. 1



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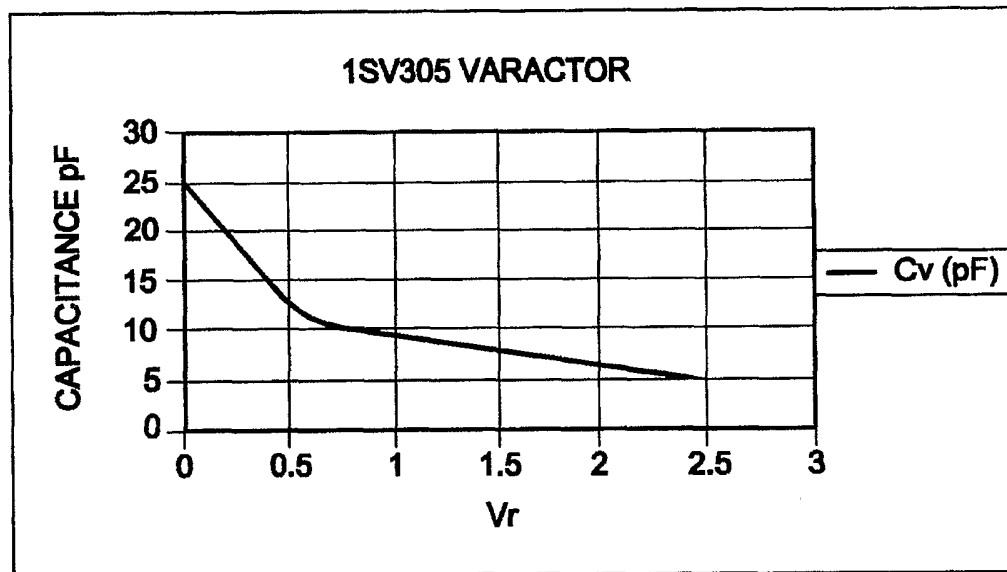


FIG. 2

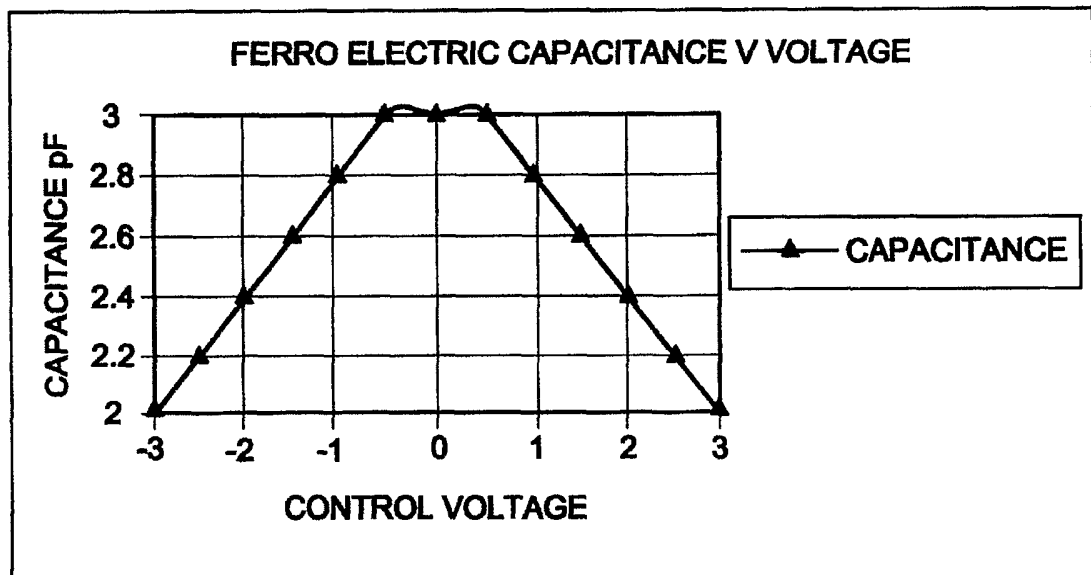
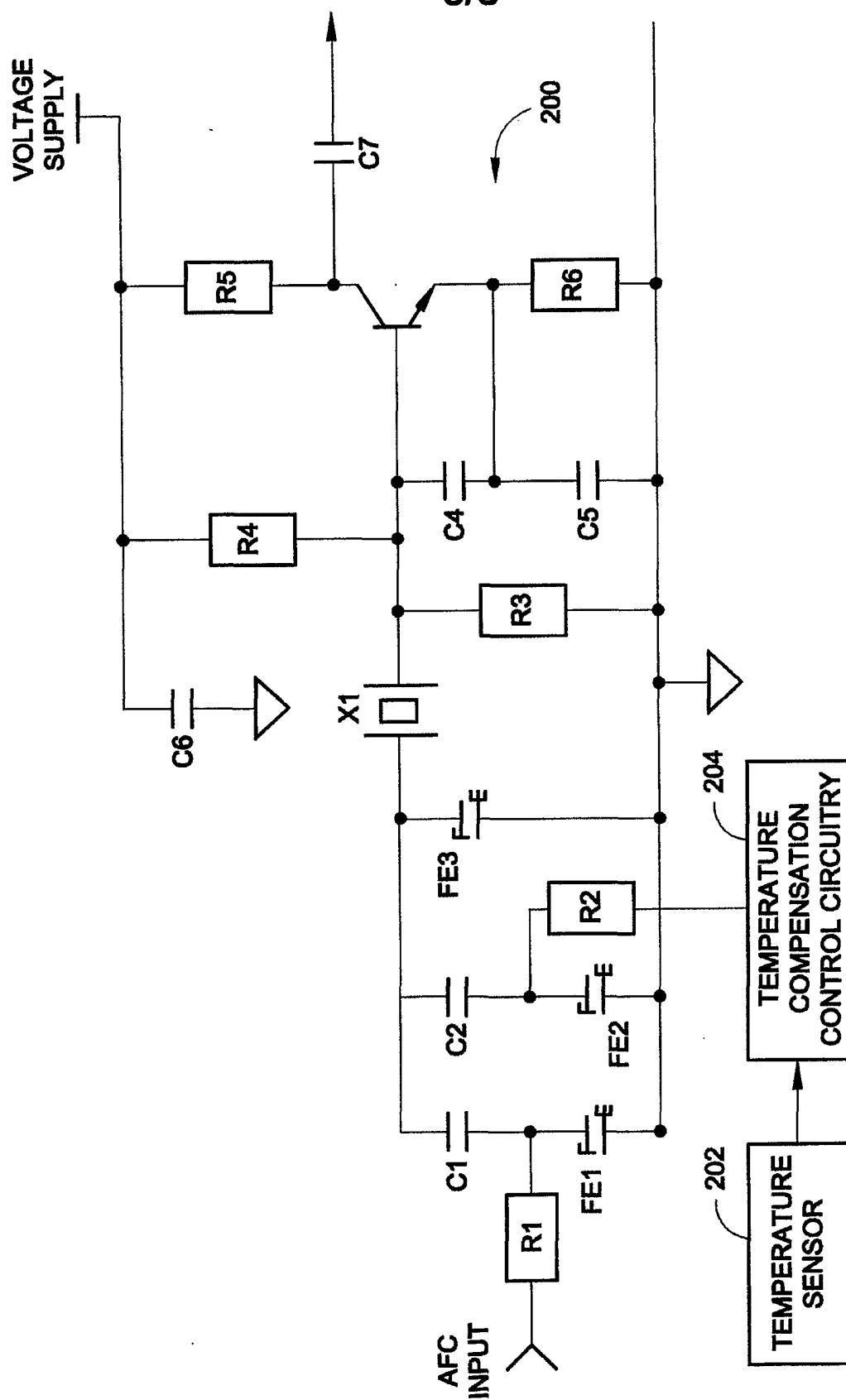


FIG. 3



**FIG. 4**

## INTERNATIONAL SEARCH REPORT

International Application No

PCT/IB 02/01119

A. CLASSIFICATION OF SUBJECT MATTER  
 IPC 7 H03B5/36 H03B5/04

According to International Patent Classification (IPC) or to both national classification and IPC

## B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

IPC 7 H03B H01L

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

EPO-Internal, PAJ, WPI Data

## C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	EP 1 043 741 A (PHILIPS CORP INTELLECTUAL PTY ;KONINKL PHILIPS ELECTRONICS NV (NL)) 11 October 2000 (2000-10-11) abstract; figures 1,2 column 3, line 43 - line 52	1-3
Y	column 3, line 13 - line 16 ---	4-19
Y	US 5 777 524 A (SUTLIFF RICHARD N ET AL) 7 July 1998 (1998-07-07) column 5, line 36-40; figure 2 ---	4-7, 15-19
Y	US 6 052 036 A (BENGTSSON ERIK ET AL) 18 April 2000 (2000-04-18) abstract; figure 1 column 2, line 19-28 column 4, line 17-30 -----	8-14

☐ Further documents are listed in the continuation of box C.

☒ Patent family members are listed in annex.

## \* Special categories of cited documents :

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Patent document cited in search report		Publication date	Patent family member(s)	Publication date
EP 1043741	A	11-10-2000	DE 19915247 A1	05-10-2000
			EP 1043741 A2	11-10-2000
			JP 2000348973 A	15-12-2000
<hr/>				
US 5777524	A	07-07-1998	CN 1211354 A	17-03-1999
			EP 0886921 A1	30-12-1998
			JP 2000507073 T	06-06-2000
			WO 9827652 A1	25-06-1998
<hr/>				
US 6052036	A	18-04-2000	AU 9655798 A	24-05-1999
			BR 9813329 A	22-08-2000
			CN 1277752 T	20-12-2000
			EE 200000188 A	16-04-2001
			EP 1025635 A1	09-08-2000
			JP 2001522185 T	13-11-2001
			NO 20002277 A	29-06-2000
			WO 9923753 A1	14-05-1999
<hr/>				